



America Semiconductor

Silicon Standard Recovery Diode

1N3212 thru
1N3214R

$V_{RRM} = 50\text{ V} - 600\text{ V}$

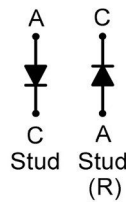
$I_F = 15\text{ A}$

Features

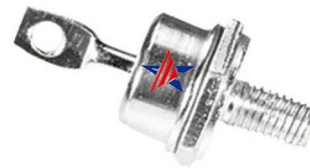
- High Surge Capability
- Types up to 600 V V_{RRM}

Note:

1. Standard polarity: Stud is cathode.
2. Reverse polarity (R): Stud is anode.
3. Stud is base.



DO-5 Package



Maximum ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	1N3212 (R)	1N3213 (R)	1N3214 (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		400	500	600	V
RMS reverse voltage	V_{RMS}		280	350	420	V
DC blocking voltage	V_{DC}		400	500	600	V
Continuous forward current	I_F	$T_C \leq 150\text{ }^\circ\text{C}$	15	15	15	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ }^\circ\text{C}$, $t_p = 8.3\text{ ms}$	297	297	297	A
Operating temperature	T_j		-65 to 175	-65 to 175	-65 to 175	$^\circ\text{C}$
Storage temperature	T_{stg}		-65 to 175	-65 to 175	-65 to 175	$^\circ\text{C}$

Electrical characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	1N3212 (R)	1N3213 (R)	1N3214 (R)	Unit
Diode forward voltage	V_F	$I_F = 15\text{ A}$, $T_j = 25\text{ }^\circ\text{C}$	1.5	1.5	1.5	V
Reverse current	I_R	$V_R = 50\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$	10	10	10	μA
		$V_R = 50\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$	10	10	10	mA

Thermal characteristics

Thermal resistance, junction - ca	R_{thJC}		0.65	0.65	0.65	$^\circ\text{C/W}$
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Figure .1-Typical Forward Characteristics

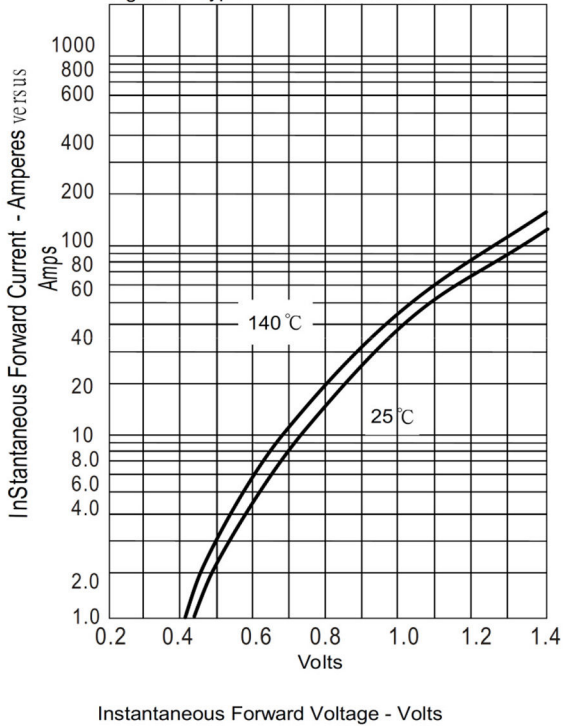


Figure .2- Forward Derating Curve

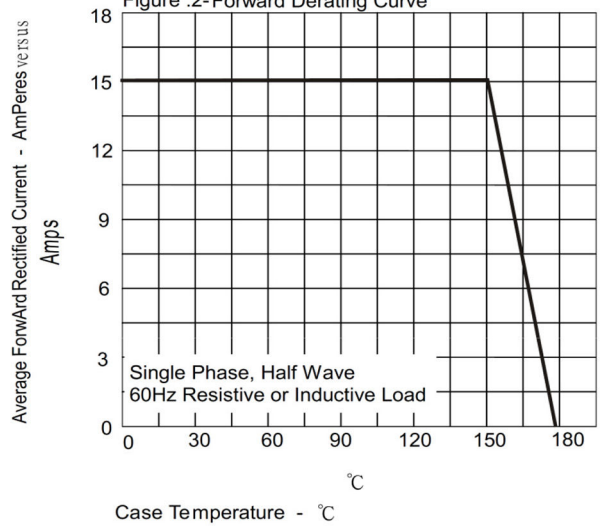


Figure .4-Typical Reverse Characteristics

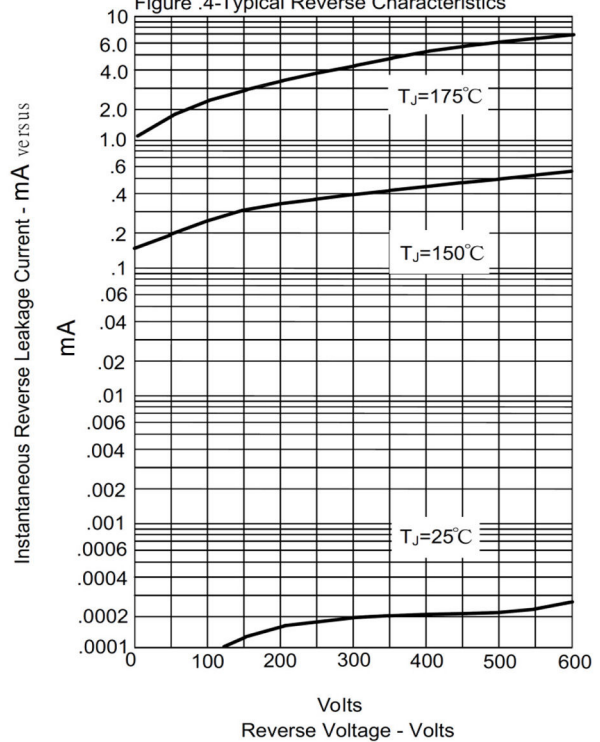


Figure .3- Peak Forward Surge Current

